1 Product profile

1.1 General description

N-channel enhancement mode common-drain dual Field-Effect Transistor (FET) in a 6 bumps Wafer Level Chip-Size Package (WLCSP) using Trench MOSFET technology.

1.2 Features and benefits

- · Common-drain type for bi-directional current flow
- · Low threshold voltage
- Ultra small package: 0.98 × 1.48 × 0.35 mm
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

1.3 Applications

- Loadswitch
- Battery Protection
- Battery Management

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{SS}	source-source voltage	T _j = 25 °C	-	-	20	V
V_{GS}	gate-source voltage		-8	_	8	V
Is	source current	$T_{amb} = 25 \text{ °C}; V_{GS} = 4.5 \text{ V}; t \le 5 \text{ s}$ [1]	-	-	5.3	Α
Static cha	Static characteristics					
R _{SSon}	source-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_S = 3 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	40	52	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².



2 Pinning information

Table 2. Pinning

Pin	Symbol	Description	Simplified outline	Graphic symbol
A1	G1	gate 1	1 2	S1 S2
A2	S1	source 1	A 🔘	M M
B1	S2	source 2	В	
B2	S1	source 1	c O	
C1	S2	source 2		G1 G2 aaa-027241
C2	G2	gate 2	Transparent top view	333 527 2 77

3 Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMCM650CUNE	WLCSP6	wafer level chip-size package; 6 bumps (3 x 2)	WLCSP6_3-2		

4 Marking

Table 4. Marking codes

Tubio 4. Marking occor			
Type number	Marking code		
PMCM650CUNE	АН		

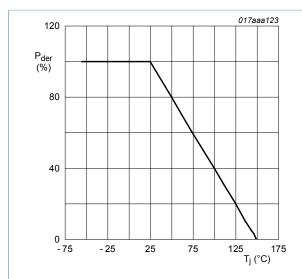
Limiting values

Table 5. Limiting values

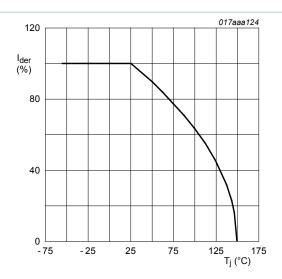
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{SS}	source-source voltage	T _j = 25 °C		-	20	V
V_{GS}	gate-source voltage	T _j = 25 °C		-8	8	V
I _S	source current	$T_{amb} = 25 ^{\circ}C; V_{GS} = 4.5 V; t \le 5 s$	[1]	-	5.3	Α
		T_{amb} = 25 °C; V_{GS} = 4.5 V	[1]	-	4.1	Α
		T_{amb} = 100 °C; V_{GS} = 4.5 V	[1]	-	2.6	Α
I _{SM}	peak source current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	16	A
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	556	mW
		T _{amb} = 25 °C	[1]	-	1300	mW
		T _{sp} = 25 °C		-	12500	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-For	rward diode			<u> </u>		
I _{FS}	source-forward current	T _{amb} = 25 °C	[1]	-	1.2	Α

Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm². Device mounted on an FR4 PCB, single-sided copper; tin-plated and standard footprint.



$$P_{der} = \frac{P_{tot}}{P_{tot(25 \, ^{\circ}C)}} \times 100\%$$



$$I_{der} = \frac{ISS}{ISS(25 \, ^{\circ}C)} \times 100\%$$

Figure 1. Normalized total power dissipation as a function of junction temperature

Figure 2. Normalized continuous source-source current as a function of junction temperature

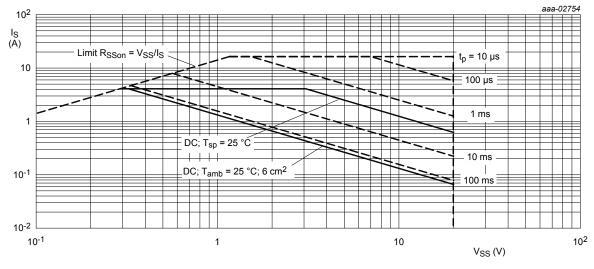


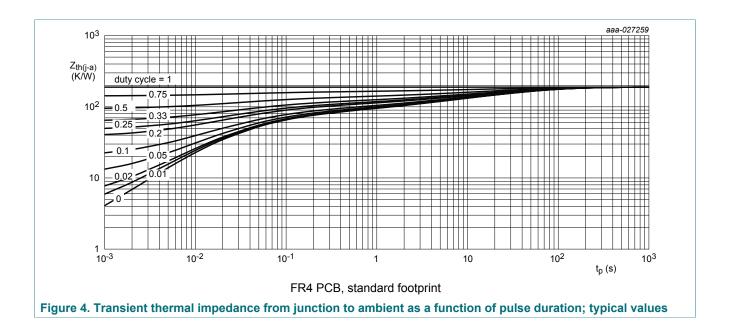
Figure 3. Safe operating area; junction to ambient; continuous and peak source currents as a function of source-source voltage

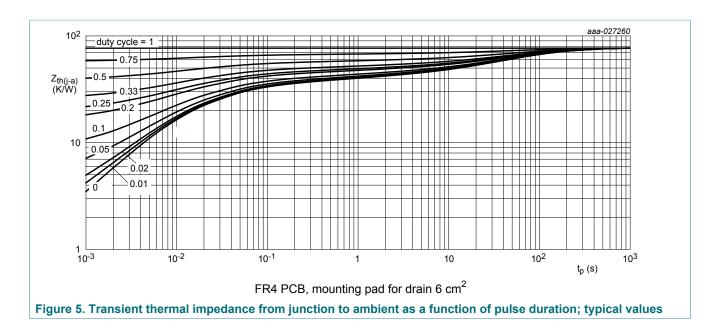
6 Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction	in free air	[1]	-	180	225	K/W
to ambient		[2]	-	65	85	K/W	
			[3]	-	75	95	K/W
	in free air; t ≤ 5 s	[3]	-	45	55	K/W	
R _{th(j-sp)}	thermal resistance from junction to solder point			-	5	10	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper; tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain, 4 layer, 1 cm².
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².



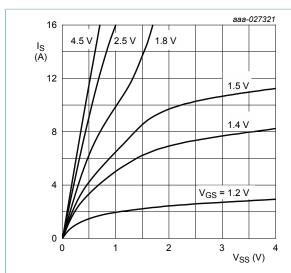


7 Characteristics

Table 7. Characteristics

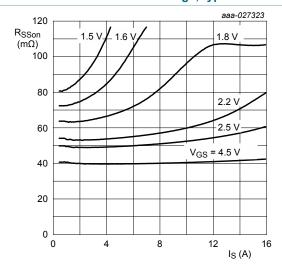
 T_i = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristic					
V _{(BR)SS}	source-source breakdown voltage	I _S = 250 μA; V _{GS} = 0 V;	20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \ \mu A; \ V_{SS} = V_{GS}$	0.4	0.7	0.9	V
I _{SSS}	source leakage current	V _{GS} = 0 V; V _{SS} = 20 V	-	-	1	μA
I _{GSS}	gate leakage current	V _{GS} = 8 V; V _{SS} = 0 V	-	-	10	μA
		$V_{GS} = -8 \text{ V}; V_{SS} = 0 \text{ V}$	-	-	-10	μA
		$V_{GS} = 4.5 \text{ V}; V_{SS} = 0 \text{ V}$	-	-	1	μΑ
		$V_{GS} = -4.5 \text{ V}; V_{SS} = 0 \text{ V}$	-	-	-1	μΑ
		$V_{GS} = 2.5 \text{ V}; V_{SS} = 0 \text{ V}$	-	-	200	nA
		$V_{GS} = -2.5 \text{ V}; V_{SS} = 0 \text{ V}$	-	-	-200	nA
R _{SSon}	source-source on-state	$V_{GS} = 4.5 \text{ V}; I_S = 3 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	40	52	mΩ
resistance	resistance	V_{GS} = 4.5 V; I_S = 3 A; T_j = 150 °C	-	55	71	mΩ
		V_{GS} = 2.5 V; I_S = 2 A; T_j = 25 °C	-	50	62	mΩ
		V_{GS} = 1.8 V; I_S = 1 A; T_j = 25 °C	-	63	95	mΩ
g _{fs}	forward transconductance	V _{GS} = 4.5 V; I _S = 3 A	-	22	-	S
R_G	gate resistance	f = 1 MHz	-	6.6	-	Ω
Dynamic (characteristics					
Q _{G(tot)}	total gate charge	V _{SS} = 10 V; I _S = 3 A; V _{GS} = 4.5 V	-	9	13	nC
Q _{GS}	gate-source charge		-	0.7	-	nC
Q_{GD}	gate-drain charge		-	2.9	-	nC
C _{iss}	input capacitance	V _{SS} = 10 V; f = 1 MHz; V _{GS} = 0 V	-	480	-	pF
C _{oss}	output capacitance		-	96	-	pF
C _{rss}	reverse transfer capacitance		-	96	-	pF
t _{d(on)}	turn-on delay time	V _{SS} = 10 V; I _S = 3 A;	-	6	-	ns
t _r	rise time	$V_{GS} = 4.5 \text{ V}; R_{G(ext)} = 6 \Omega$	-	20	-	ns
t _{d(off)}	turn-off delay time		-	39	-	ns
t _f	fall time		-	15	-	ns
Source-Fo	oward diode		1			
V _{FS}	source-forward voltage	$V_{G1S1} = 0 \text{ V}$; $V_{G2S2} = 4.5 \text{ V}$; $I_S = 1.2 \text{ A}$	-	0.7	1.2	V



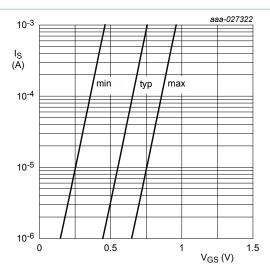
 $T_i = 25 \,^{\circ}C$

Figure 6. Output characteristics: source current as a function of source-source voltage; typical values



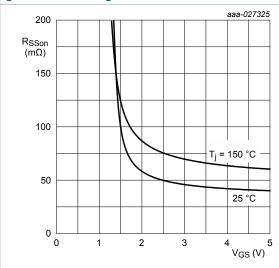
 $T_i = 25 \,^{\circ}C$

Figure 8. Source-source on-state resistance as a function of source current; typical values



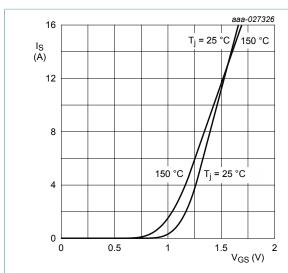
 V_{SS} = 5 V; T_i = 25 °C

Figure 7. Sub-threshold source current as a function of gate-source voltage



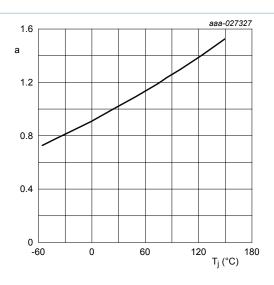
 $I_S = 3 A$

Figure 9. Source-source on-state resistance as a function of gate-source voltage; typical values



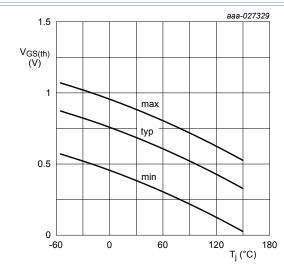
 $V_{SS} > I_S \times R_{SSon}$

Figure 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



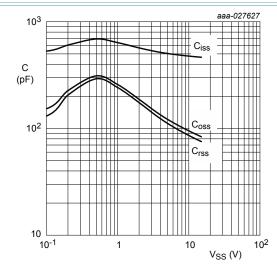
$$a = \frac{RSSon}{RSSon(25 \,^{\circ}C)} \times 100\%$$

Figure 11. Normalized source-source on-state resistance as a function of junction temperature; typical values



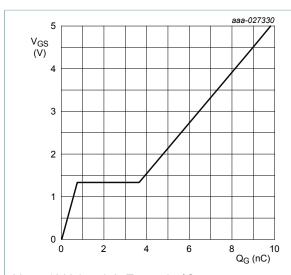
 $I_S = 250 \mu A; V_{SS} = V_{GS}$

Figure 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Figure 13. Input, output and reverse transfer capacitances as a function of source-source voltage; typical values



 V_{SS} = 10 V; I_S = 3 A; T_{amb} = 25 °C

Figure 14. Gate-source voltage as a function of gate charge; typical values

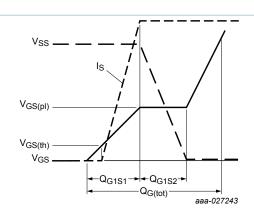
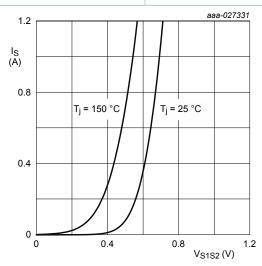


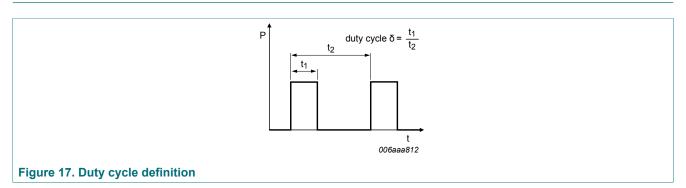
Figure 15. Common Drain MOSFET gate charge definitions



 $V_{G1S1} = 0 V; V_{G2S2} = 4.5 V$

Figure 16. Source current as a function of source-source voltage; typical values

8 Test information

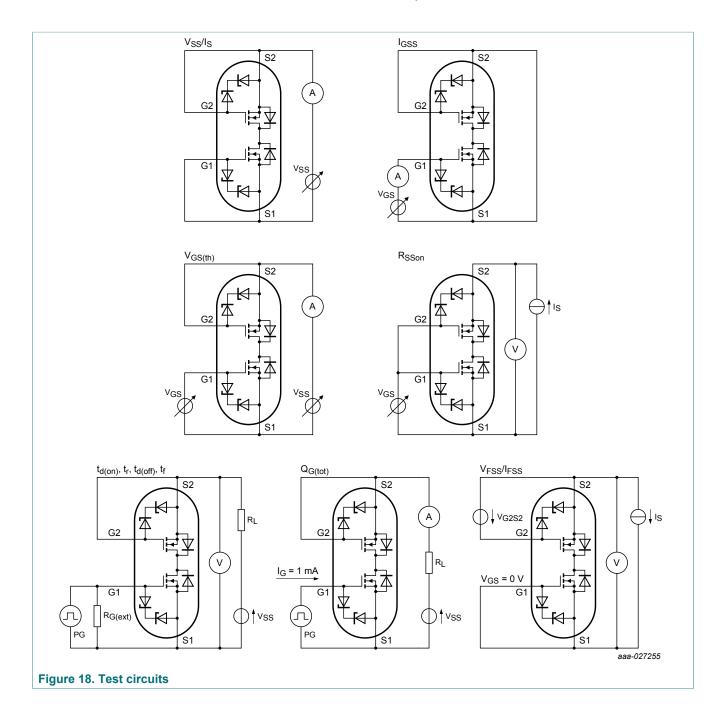


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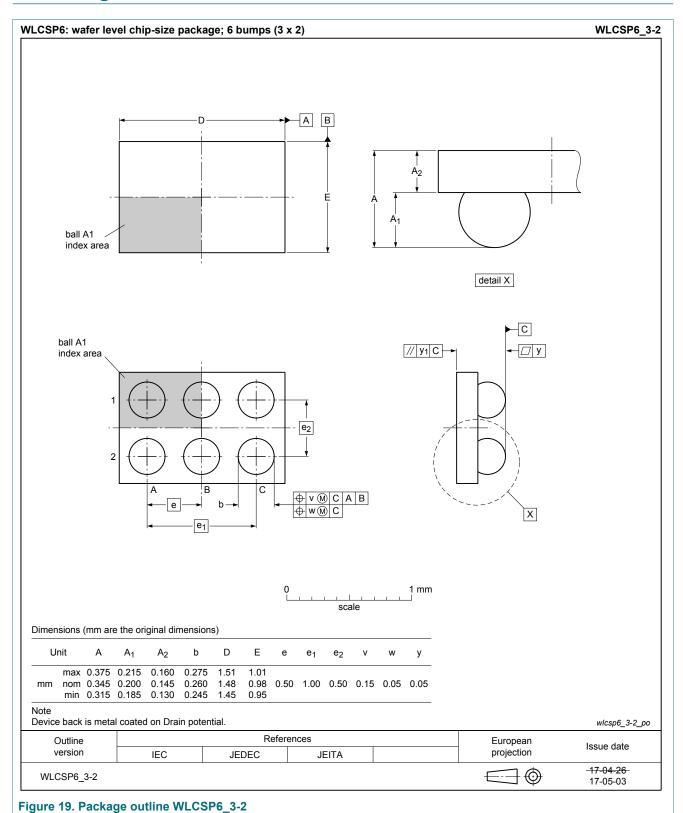
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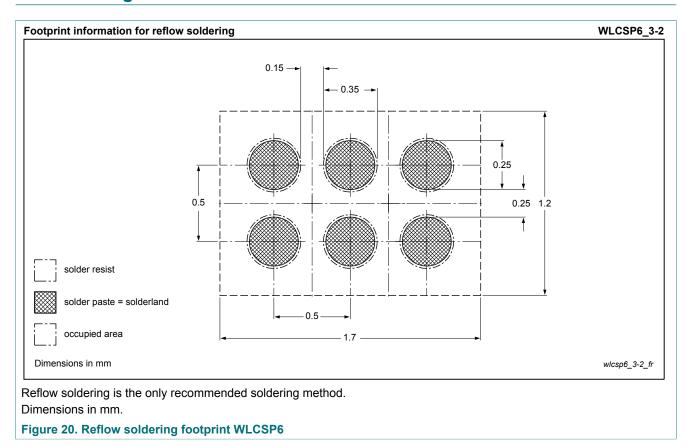
10 / 18



9 Package outline



10 Soldering



PMCM650CUNE

20 V, Common Drain N-channel Trench MOSFET

11 Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMCM650CUNE v.1	20171108	Product data sheet	-	-

12 Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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20 V, Common Drain N-channel Trench MOSFET

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